

# **BC847BPN-QF Datasheet**

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DiGi Electronics Part Number BC847BPN-QF-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number BC847BPN-QF

Description TRANS NPN/PNP 45V 0.1A 6TSSOP

**Detailed Description** Bipolar (BJT) Transistor Array NPN, PNP 45V 100mA

100MHz 200mW Surface Mount 6-TSSOP



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# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
BC847BPN-QF	Nexperia USA Inc.
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
NPN, PNP	100mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
45V	300mV @ 5mA, 100mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
15nA (ICBO)	200 @ 2mA, 5V
Power - Max:	Frequency - Transition:
200mW	100MHz
Operating Temperature:	Grade:
150°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount
Package / Case:	Supplier Device Package:
6-TSSOP, SC-88, SOT-363	6-TSSOP
Base Product Number:	
BC847	

# **Environmental & Export classification**

8541.21.0075

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



# 1. General description

NPN/PNP general-purpose transistor pair in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

#### 2. Features and benefits

- · Low collector capacitance
- Low collector-emitter saturation voltage
- · Closely matched current gain
- · Reduces number of components and board space
- No mutual interference between the transistors
- · Qualified according to AEC-Q101 and recommended for use in automotive applications

# 3. Applications

General-purpose switching and amplification

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor; for the PNP transistor with negative polarity							
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	45	V
I <sub>C</sub>	collector current			-	-	100	mA
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		200	-	450	



# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1		C1 B2 E2
2	B1	base TR1	<u> </u>	
3	C2	collector TR2		(TR1)
4	E2	emitter TR2		
5	B2	base TR2	∐1 ∐2 ∐3	
6	C1	collector TR1	TSSOP6 (SOT363)	sym139

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
BC847BPN-Q		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363		

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
BC847BPN-Q	13%

[1] % = placeholder for manufacturing site code

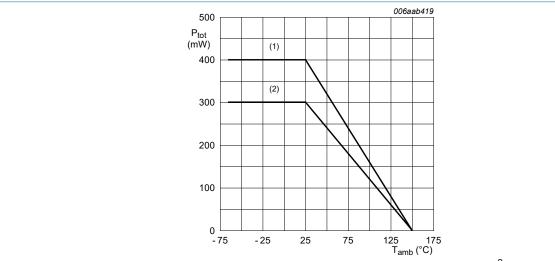
# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transiste	or; for the PNP transistor wit	h negative polarity			'	
V <sub>CBO</sub>	collector-base voltage	open emitter		-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	45	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	5	V
I <sub>C</sub>	collector current			-	100	mA
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	200	mA
I <sub>BM</sub>	peak base current	-		-	200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	220	mW
			[2]	-	250	mW
Per device			,		'	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	300	mW
			[2]	-	400	mW
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided, 35 μm copper, tin-plated, mounting pad for collector 1 cm².



- (1) FR4 PCB, single-sided, 35 µm copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>
- (2) FR4 PCB, single-sided, 35  $\mu m$  copper, tin-plated and standard footprint

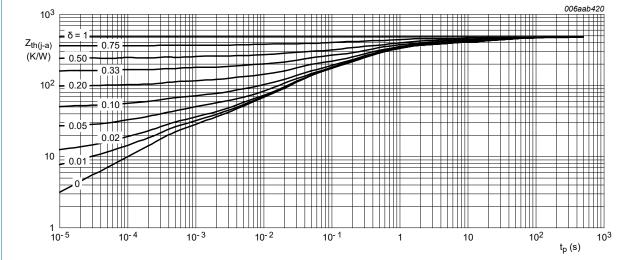
Fig. 1. Per device: Power derating curves SOT363 (SC-88)

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

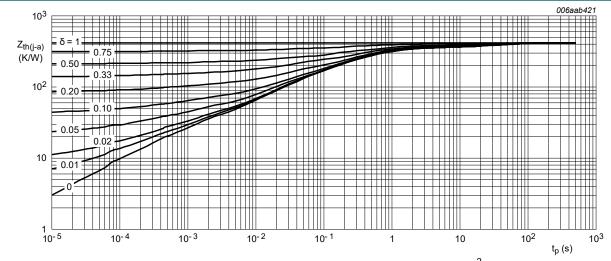
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or		,		'		'
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	-	568	K/W
junction to ambient		[2]	-	-	500	K/W	
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	230	K/W
Per device							'
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	-	416	K/W
	junction to ambient		[2]	-	-	313	K/W

- [1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided, 35 μm copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.



FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint

Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, single-sided, 35 µm copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>

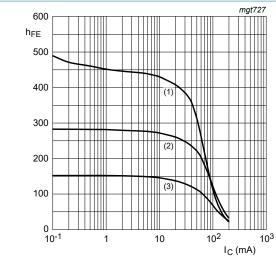
Fig. 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

# 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	or; for the PNP transistor v	with negative polarity				
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	$I_C = 100 \ \mu\text{A}; \ I_E = 0 \ \text{A}; \ T_{amb} = 25 \ ^{\circ}\text{C}$	50	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	45	-	-	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_C = 0 \text{ A}; I_E = 100 \mu\text{A}; T_{amb} = 25 \text{ °C}$	5	-	-	V
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 30 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	15	nA
	current	V <sub>CB</sub> = 30 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 2 mA; T <sub>amb</sub> = 25 °C	200	-	450	
V <sub>CEsat</sub>	collector-emitter	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0.5 mA; T <sub>amb</sub> = 25 °C	-	-	100	mV
	saturation voltage	$I_C$ = 100 mA; $I_B$ = 5 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	-	-	300	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$	-	755	-	mV
V <sub>BE</sub>	base-emitter voltage	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 2 mA; T <sub>amb</sub> = 25 °C	580	655	700	mV
			600	655	750	mV
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz;	-	-	1.5	pF
		T <sub>amb</sub> = 25 °C	-	-	2.2	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_C = 0 \text{ A}; i_c = 0 \text{ A};$	-	11	-	pF
		f = 1 MHz; T <sub>amb</sub> = 25 °C	-	10	-	pF
f <sub>T</sub>	transition frequency	$V_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA; } f = 100 \text{ MHz;}$ $T_{amb} = 25 \text{ °C}$	100	-	-	MHz

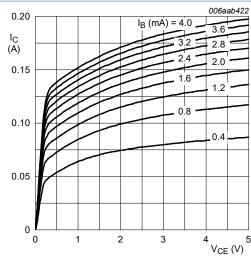
5 / 13



$$V_{CE} = 5 V$$

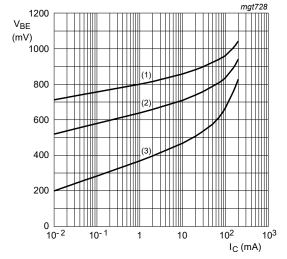
(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

NPN transistor: DC current gain as a function of Fig. 4. collector current; typical values



 $T_{amb}$  = 25 °C

Fig. 5. NPN transistor: Collector current as a function of collector-emitter voltage; typical values



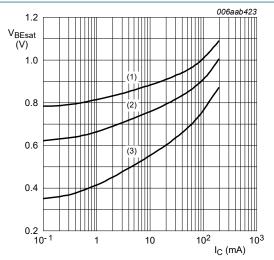


(1) 
$$T_{amb}$$
 = -55 °C

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 150 \, ^{\circ}C$ 

Fig. 6. Base-emitter voltage as a function of collector current; typical values



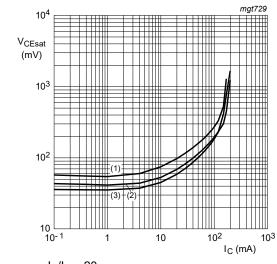
$$I_{\rm C}/I_{\rm B}=20$$

$$(1) T_{amb} = -55 °C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 150 \, ^{\circ}C$ 

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

$$I_{C}/I_{B} = 20$$
(1)  $T_{amb} = 150 \,^{\circ}C$ 
(2)  $T_{amb} = 25 \,^{\circ}C$ 
(3)  $T_{amb} = -55 \,^{\circ}C$ 

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

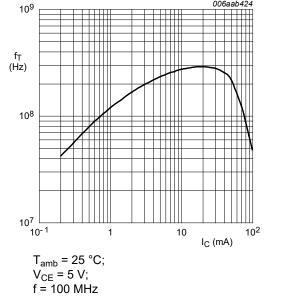
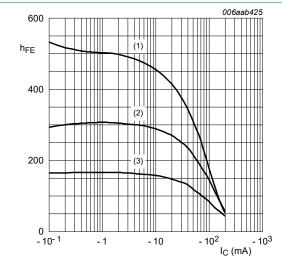


Fig. 9. Transition frequency as a function of collector current; typical values



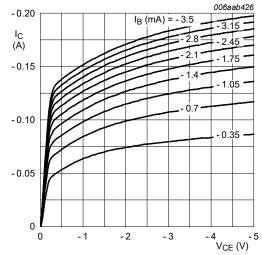
 $V_{CE}$  = -5 V

(1)  $T_{amb} = 150 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -55 \,^{\circ}C$ 

Fig. 10. PNP transistor: DC current gain as a function of collector current; typical values



T<sub>amb</sub> = 25 °C

Fig. 11. PNP transistor: Collector current as a function of collector-emitter voltage; typical values

**Nexperia** BC847BPN-Q

#### 45 V, 100 mA NPN/PNP general-purpose transistor

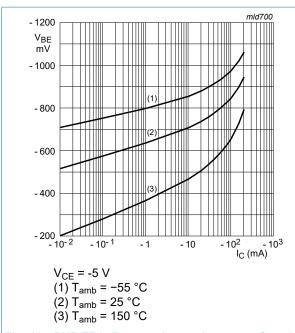


Fig. 12. PNP TR2: Base-emitter voltage as a function of collector current; typical values

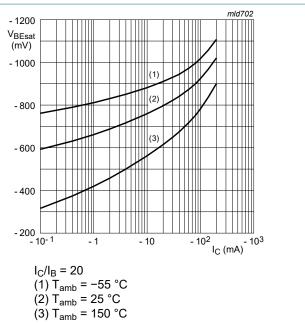


Fig. 13. PNP TR2: Base-emitter saturation voltage as a function of collector current; typical values

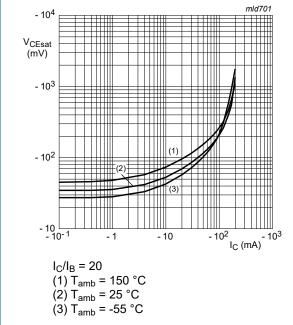


Fig. 14. PNP TR2: Collector-emitter saturation voltage as a function of collector current; typical values

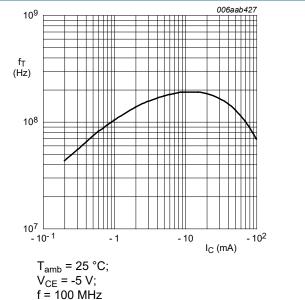


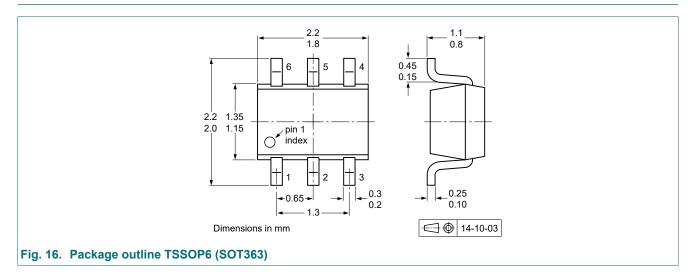
Fig. 15. PNP transistor: Transition frequency as a function of collector current; typical values

## 11. Test information

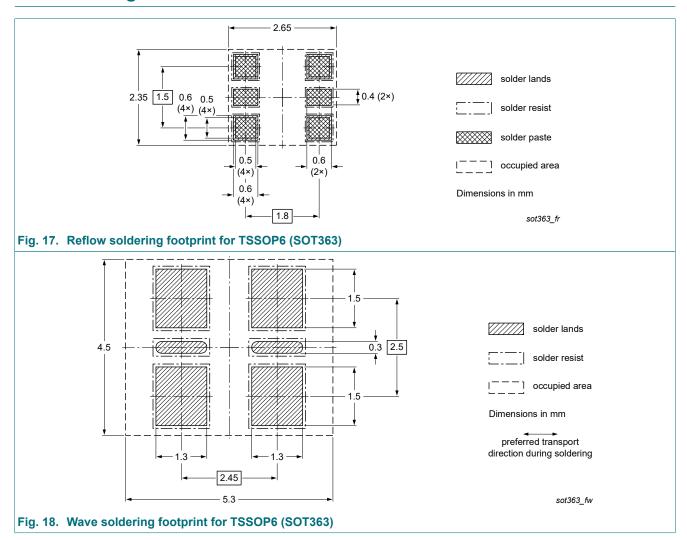
#### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

# 12. Package outline



# 13. Soldering



Nexperia

BC847BPN-Q

45 V, 100 mA NPN/PNP general-purpose transistor

# 14. Revision history

## Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BC847BPN-Q v.1	20210617	Product data sheet	-	-

# 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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# Nexperia

# BC847BPN-Q

#### 45 V, 100 mA NPN/PNP general-purpose transistor

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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 17 June 2021

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